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T.S.

Docket: 0756-2064

CERTIFICATE OF MAILING

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Cameron S. Gilligan

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/437,135) Group Art Unit:
Filed: November 10, 1999) Examiner:
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR FORMING THE)
SAME) Date: March 2, 2000

SUPPLEMENT TO PRIOR INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents

Washington, D.C. 20231

Sir:

In addition to the information disclosure statement filed on February 14, 2000, Applicants provide the following concise explanation of the references cited therein:

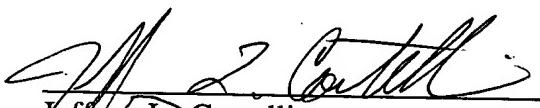
JP 63-211756 teaches forming an oxide film on a semiconductor substrate and annealing in a nitrogen atmosphere.

JP 49-78483 teaches forming the oxide film containing halogen on the semiconductor substrate by ion implantation of the halogen.

However, neither of these references teaches the allowable subject matter that nitriding only the vicinity of the silicon oxide film. Although, JP 63-211756 teaches the annealing in a nitrogen atmosphere, Applicants contend that it never teaches intentional nitriding by introducing nitrogen ion into the vicinity of the silicon oxide film.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,



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